

Features

- Excellent hFE linearity
- Complements the 2SC5658



SOT-723

Absolute Maximum Ratings(TA=25℃)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current	-0.15	A
P _C	Collector Power Dissipation	150	mW
T _J , T _{stg}	Operation Junction And Storage Temperature Range	-55 ~ +150	℃

Electrical Characteristics (TA=25℃ unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-50μA, I _E =0	-60			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA, I _B =0	-50			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-50μA, I _C =0	-6			V
I _{CBO}	Collector cut-off current	V _{CB} =-60V, I _E =0			-0.1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V, I _C =0			-0.1	μA
h _{FE}	DC current gain	V _{CE} =-6V, I _C =-1.0mA	120		560	
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-50mA, I _B =-5mA			-0.5	V
f _T	Transition frequency	V _{CE} =-12V, I _C =-2mA, f=30MHz		140		MHz
C _{ob}	Collector output capacitance	V _{CB} =-12V, I _E =0, f=1MHz			5	pF

Ordering information

Product ID	Pack	Naming rule	Marking	hFE(1)	Qty(PCS)
2SA2029	SOT-723	2SA2029 ↓ 产品名称 product name	FR	180-390	8000



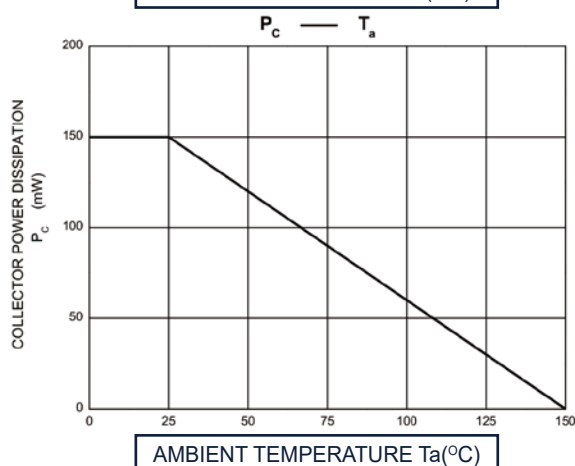
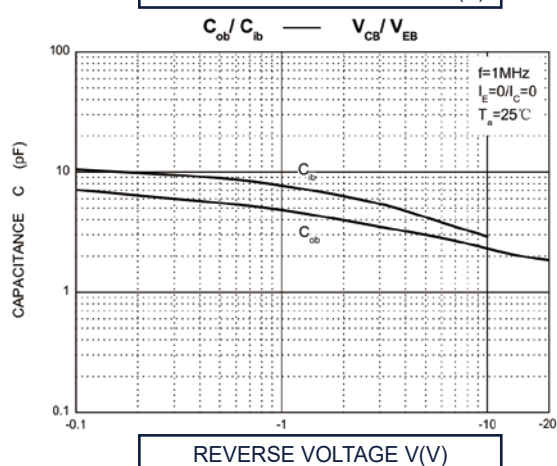
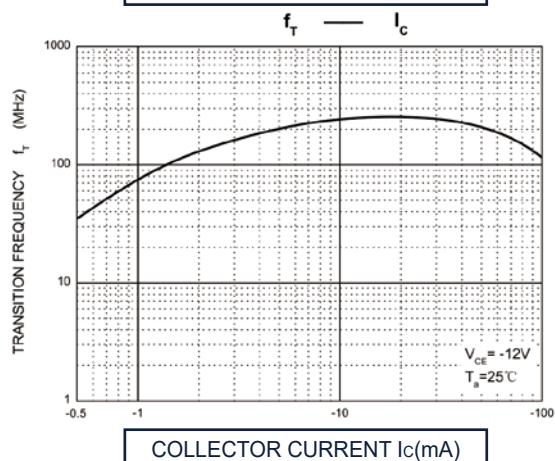
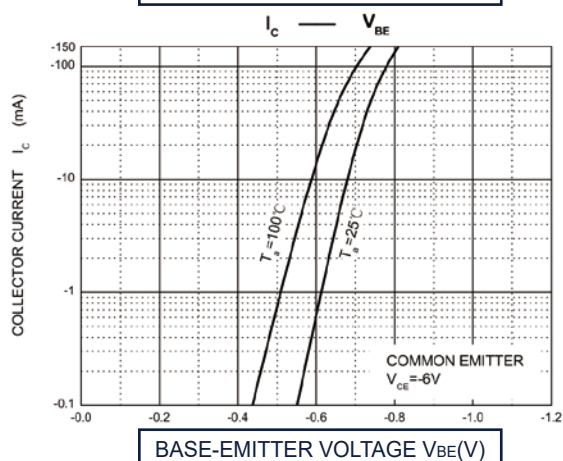
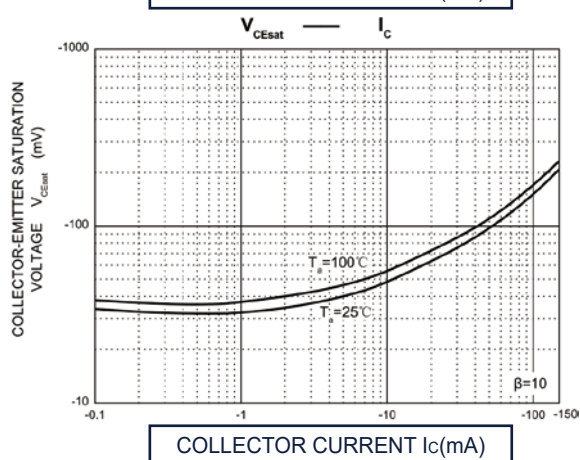
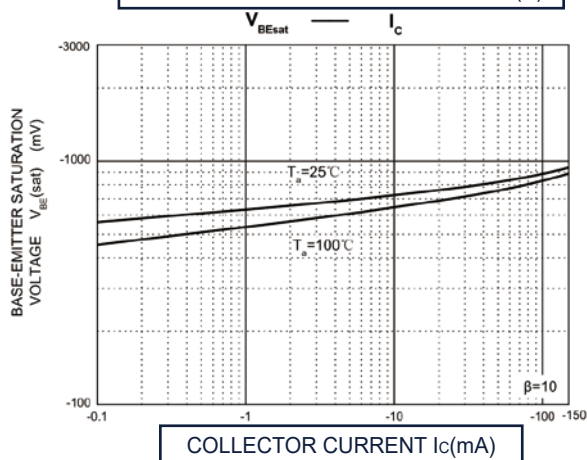
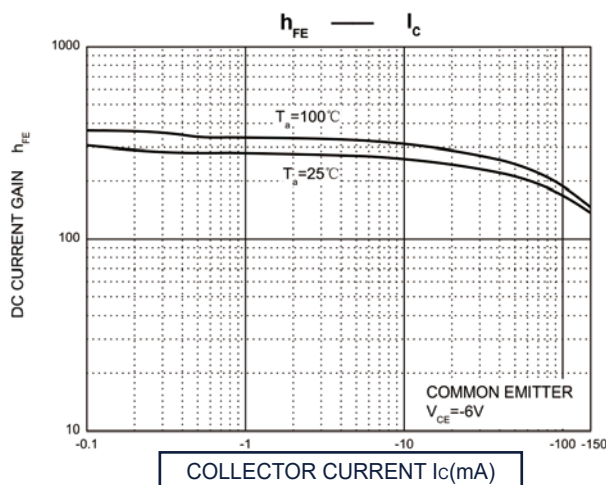
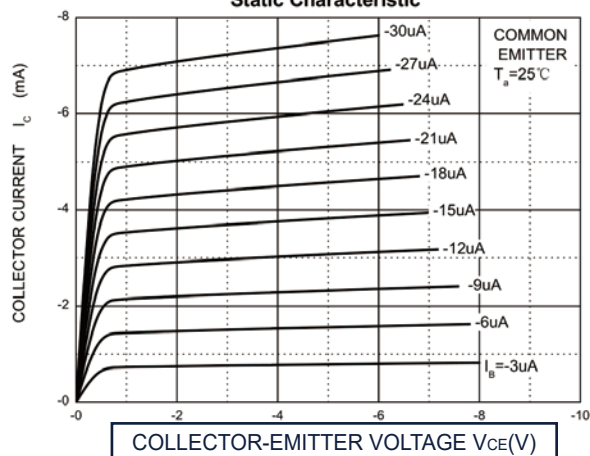
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TL-2SA2029

SOT-723 Plastic-Encapsulate Transistors (PNP)

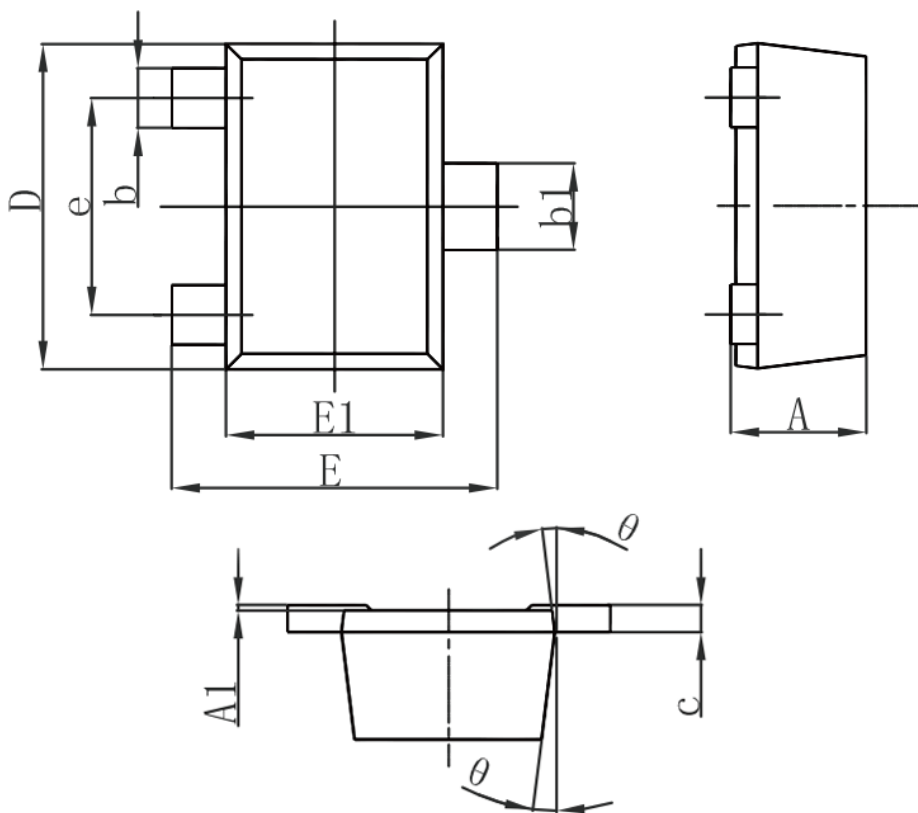
Typical Characteristics

Static Characteristic





SOT-723 Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A		0.500		0.020
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
c		0.150		0.006
D	1.150	1.250	0.045	0.045
E	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
e	0.800TYP.		0.031TYP.	
θ	7° REF.		7° REF.	